

2SC4278

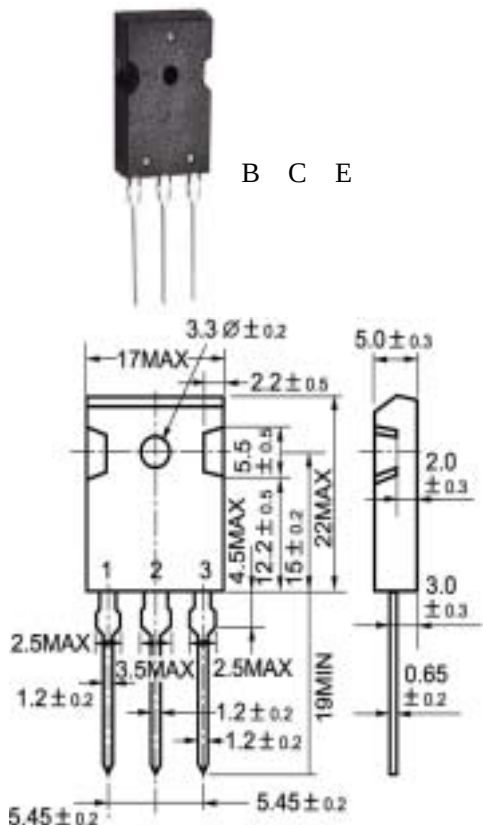
Silicon NPN Transistors

◆ Features

- With TO-247 package
- Complement to type 2SA1633

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	150	V
V_{CEO}	Collector to emitter voltage	150	V
V_{CER}	Emitter to base voltage		
V_{EB}	Emitter to base voltage	5	V
I_B	Base Current		
I_C	Collector current-Continuous	10	A
P_D	Total Power Dissipation@TC=25℃ Derate above 25℃	100	W W/℃
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-65~150	℃



TO-247

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30mA; I_B=0$	150		V
V_{CBO}	Collector-Base Voltage	$I_C=1mA; I_E=0$	150		V
I_{CEO}	Collector Cutoff Current	$V_{CE}=150V; I_B=0$		500	uA
I_{CBO}	Collector Cutoff Current	$V_{CB}=150V; I_E=0$		100	uA
I_{EBO}	Emitter Cutoff Current				
V_{EBO}	Emitter Cutoff Current	$I_E=5mA; I_C=0$	5		V
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	$I_C=5A; I_B=0.5A$		2.0	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages				
$V_{CE(sat-3)}$	Collector-emitter saturation voltages				
$V_{CE(sat-4)}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	$I_C=1A; V_{CE}=5V$	60	320	
h_{FE-2}	Forward current transfer ratio				
$V_{BE(sat)}$	Base-emitter Saturation voltages				
f_T	Current Gain-Bandwidth Product				